



Phase Control Thyristor

DS5809-2 April 2013 (LN30260)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR3790B42 DCR3790B40 DCR3790B35 DCR3790B30	4200 4000 3500 3000	$\begin{split} T_{vj} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \\ I_{DRM} = I_{RRM} = 200\text{mA}, \\ V_{DRM}, V_{RRM} t_p = 10\text{ms}, \\ V_{DSM} \& V_{RSM} = \\ V_{DRM} \& V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR3790B42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	4200V
$I_{T(AV)}$	3790A
I _{TSM}	53500A
dV/dt*	1500V/µs
dl/dt	400A/μs

* Higher dV/dt selections available

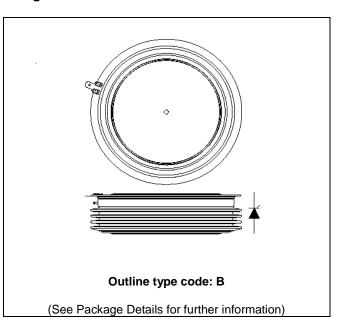


Fig. 1 Package outline





CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	3790	А
I _{T(RMS)}	RMS value	-		А
I _T	Continuous (direct) on-state current	-	5330	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	53.5	kA
l ² t	I ² t for fusing	$V_R = 0$	14.31	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.007	°C/W
		Single side cooled	Anode DC	-	0.0116	°C/W
			Cathode DC	-	0.0181	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 70.0kN	Double side	-	0.0014	°C/W
		(with mounting compound)	Single side	-	0.0028	°C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			63.0	77.0	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	Test Conditions		Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	200	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	1500	V/µs
dI/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	400	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
$V_{T(TO)}$	Threshold voltage – Low level	700A to 4100A at T _{case} = 125	5°C	-	0.83	٧
	Threshold voltage – High level	4100A to 12000A at T _{case} = 125°C		-	1.0	V
r _T	On-state slope resistance – Low level	700A to 4100A at T _{case} = 125°C		-	0.1688	mΩ
	On-state slope resistance – High level	4100A to 12000A at T _{case} = 125°C		-	0.1263	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω		TBD	TBD	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
t _q	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, dl/dt	= 1A/μs,	250	500	μs
		dV _{DR} /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$, $T_j = 125$ °C, $dI/dt - 1A/\mu s$,		1500	4500	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I _H	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50^{\circ}$	0A, I _T = 5A	-	300	mA



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25$ °C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

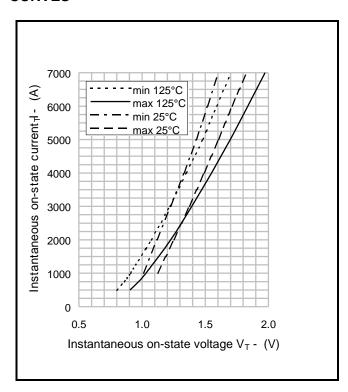


Fig.2 Maximum & minimum on-state characteristics

 V_{TM} EQUATION Where A = 0.348967 B = 0.066851

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ C = 0.000102

D = 0.003788

these values are valid for T_j = 125°C for I_T 500A to 10000A



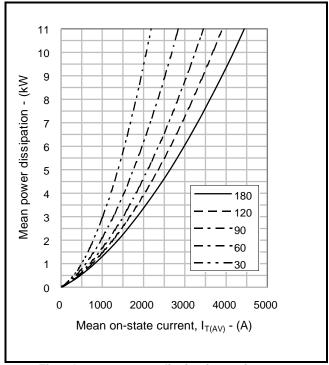


Fig.3 On-state power dissipation – sine wave

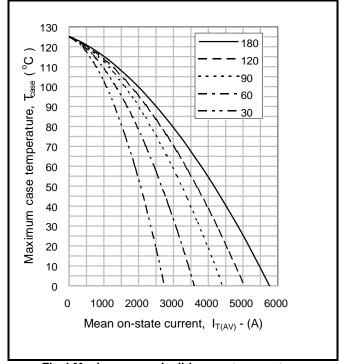


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

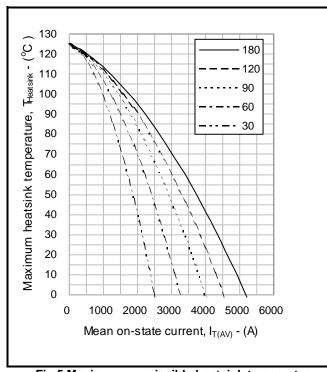


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

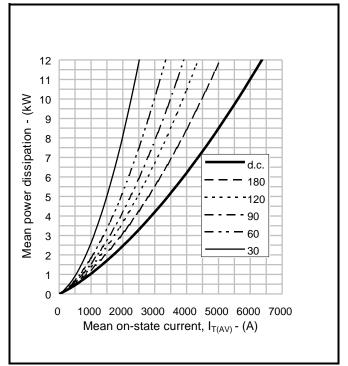
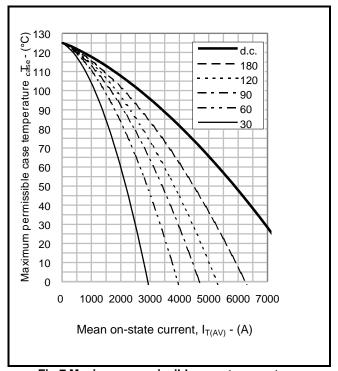
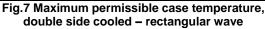


Fig.6 On-state power dissipation - rectangular wave







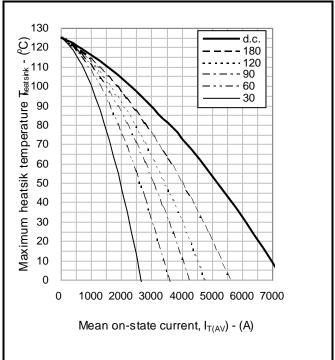
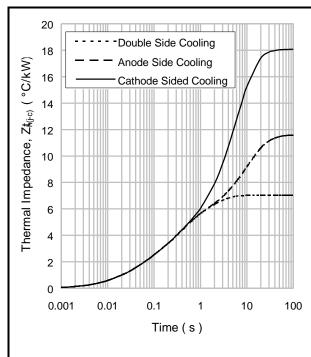


Fig.8 Maximum permissible heatsink temperature, double side cooled - rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	0.502	1.333	2.9559	2.2335
	T _i (s)	0.0137081	0.0548877	0.3311925	1.6905
Anode side cooled	R _i (°C/kW)	1.3035	3.138	1.1859	5.9136
	T _i (s)	0.0251065	0.2410256	1.0806	11.002
Cathode side cooled	R _i (°C/kW)	1.2616	2.6216	13.3603	0.8304
	T _i (s)	0.0245837	0.2005035	5.7854	16.765

 $Z_{th} = \sum_{i} [R_i x (1-exp. (t/t_i))]$ [1]

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance $R_{\text{th(j-c)}}$ when the device operates at conduction angles other than d.c.

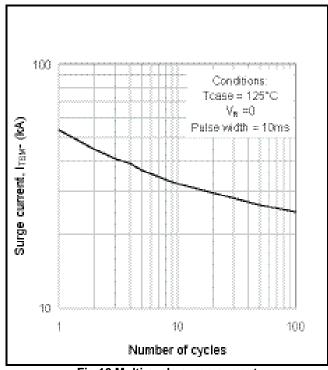
0.47 0.75

0.96

Double side cooling					Anode Side (Cooling
	$\Delta Z_{th}(z)$				ΔZ_t	_h (z)
θ°	sine.	rect.		θ°	sine.	rect
180	0.70	0.48		180	0.67	0.47
120	0.80	0.68	ĺ	120	0.77	0.66
90	0.90	0.78		90	0.87	0.75
60	1.00	0.89		60	0.95	0.86
30	1.07	1.01		30	1.02	0.96
15	1 10	1.07	ĺ	15	1.05	1.02

atno	thode Sided Cooling			
	ΔZ_{th} (z)			
	sine.	rect.		
)	0.67	0.47		
)	0.77	0.66		
	0.87	0.76		
	0.95	0.86		
	1.02	0.96		
	1.05	1.02		
)	ΔZ _t sine. 0 0.67 0 0.77 0 0.87 0.95 1.02		

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)





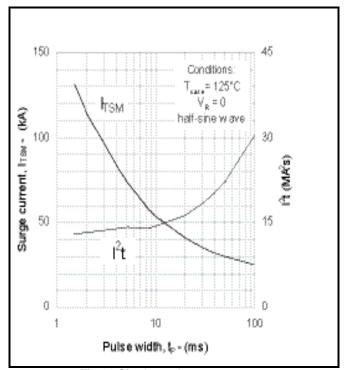


Fig.11 Single-cycle surge current

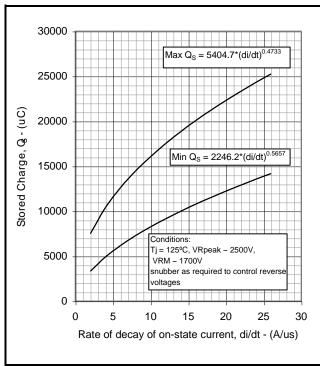


Fig.12 Stored charge

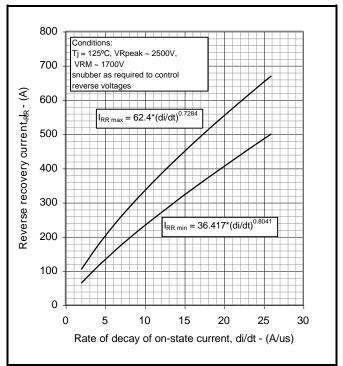


Fig.13 Reverse recovery current

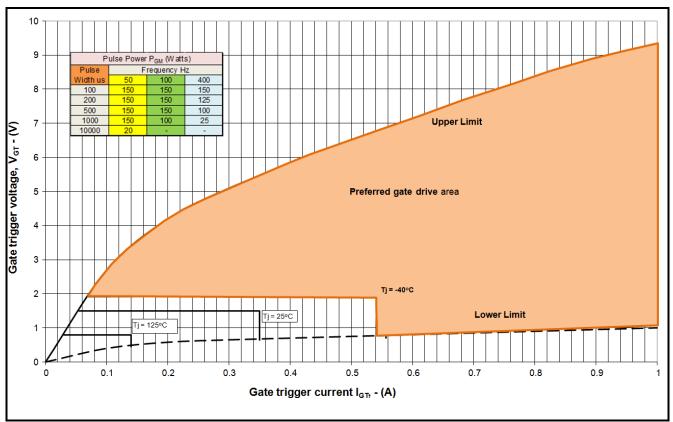


Fig14 Gate Characteristics

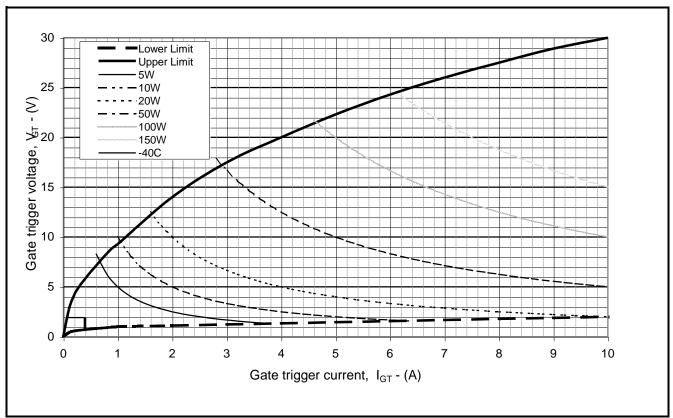


Fig. 15 Gate characteristics





PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

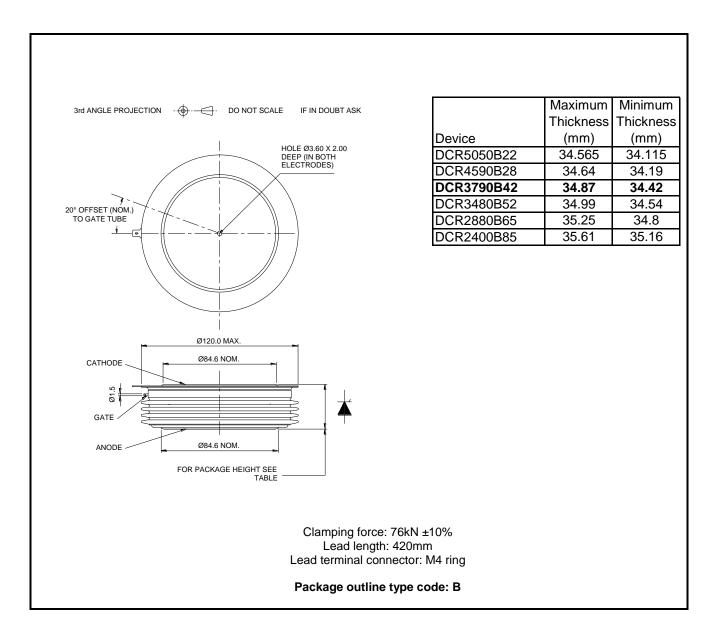


Fig.16 Package outline





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